

# MOSFET – N-Channel, POWERTRENCH®

**200 V, 62 A, 27 mΩ**

## FDP2614

### General Description

This N-Channel MOSFET is produced using onsemi's advanced POWERTRENCH process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

### Features

- $R_{DS(on)} = 22.9 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 31 \text{ A}$
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{DS(on)}$
- High Power and Current Handling Capability
- This Device is Pb-Free, Halide Free and is RoHS Compliant

### Applications

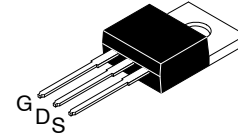
- Consumer Appliances
- Synchronous Rectification
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies

### MOSFET MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain to Source Voltage	200	V
$V_{GS}$	Gate to Source Voltage	+30	V
$I_D$	Drain Current	Continuous ( $T_C = 25^\circ\text{C}$ )	62
		Continuous ( $T_C = 100^\circ\text{C}$ )	39.3
$I_{DM}$	Drain Current	Pulsed (Note 1)	see Figure 9
$E_{AS}$	Single Pulse Avalanche Energy (Note 2)	145	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	260	W
	Derate above $25^\circ\text{C}$	2.1	W/ $^\circ\text{C}$
$T_J$ , $T_{STG}$	Operating and Storage Temperature	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

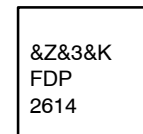
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

$V_{DS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
200 V	27 mΩ @ 10 V	62 A

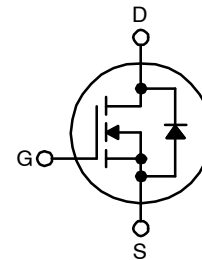


**TO-220-3LD  
 CASE 340AT**

### MARKING DIAGRAM



- &Z = Assembly Plant Code
- &3 = 3-Digit Date Code
- &K = 2-Digits Lot Run Traceability Code
- FDP2614 = Specific Device Code



**N-Channel**

### ORDERING INFORMATION

Device	Package	Shipping
FDP2614	TO-220-3LD	800 Units / Tube

# FDP2614

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance Junction to Case, Max.	0.48	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient, Max.	62.5	°C/W

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
--------	-----------	----------------	-----	-----	-----	------

### OFF CHARACTERISTICS

$B_{VDSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}, T_J = 25^\circ\text{C}$	200	-	-	V
$\frac{\Delta B_{VDSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.2	-	V/°C
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	-	-	10	$\mu\text{A}$
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$	-	-	500	
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	-	-	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	-	-	-100	nA

### ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	4.0	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 31\text{ A}$	-	22.9	27	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 31\text{ A}$	-	72	-	S

### DYNAMIC CHARACTERISTICS

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	-	5435	7230	pF
$C_{oss}$	Output Capacitance		-	505	675	pF
$C_{rss}$	Reverse Transfer Capacitance		-	110	165	pF

### SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 62\text{ A}, V_{GS} = 10\text{ V}, R_{GEN} = 25\ \Omega$ (Note 4)	-	77	165	ns
$t_r$	Turn-On Rise Time		-	284	560	ns
$t_{d(off)}$	Turn-Off Delay Time		-	103	220	ns
$t_f$	Turn-Off Fall Time		-	162	335	ns
$Q_g$	Total Gate Charge	$V_{DS} = 100\text{ V}, I_D = 62\text{ A}, V_{GS} = 10\text{ V}$ (Note 4)	-	76	99	nC
$Q_{gs}$	Gate-Source Charge		-	35	-	nC
$Q_{gd}$	Gate-Drain Charge		-	18	-	nC

### DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	-	-	62	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	-	-	186	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 62\text{ A}$	-	-	1.2	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 62\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	145	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	0.81	-	$\mu\text{C}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 1\text{ mH}, I_{AS} = 17\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 62\text{ A}, di/dt \leq 100\text{ A}/\text{ms}, V_{DD} \leq B_{VDSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Essentially Independent of Operating Temperature Typical Characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

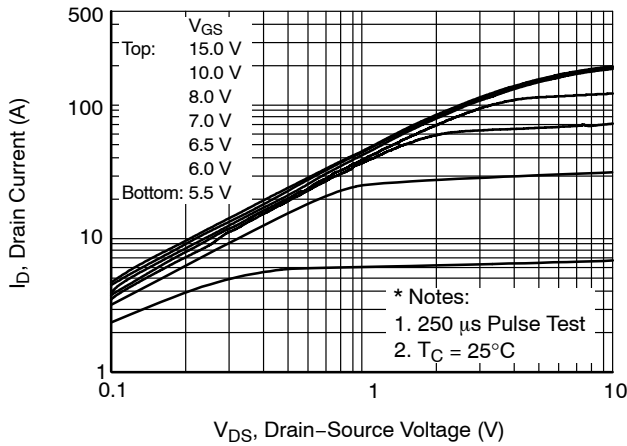


Figure 1. On-Region Characteristics

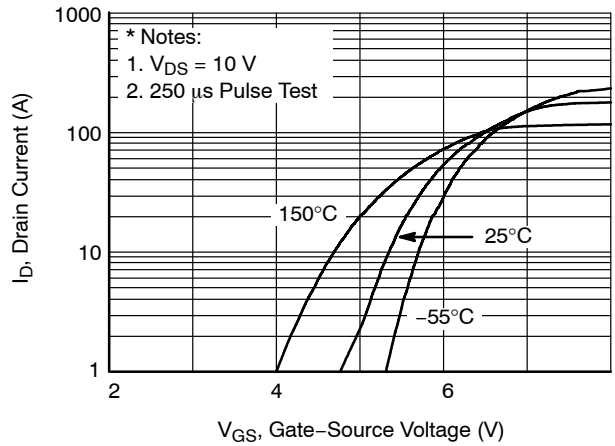


Figure 2. Transfer Characteristics

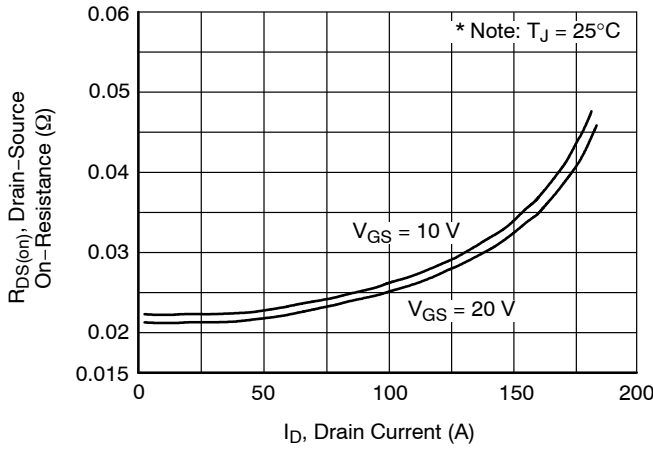


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

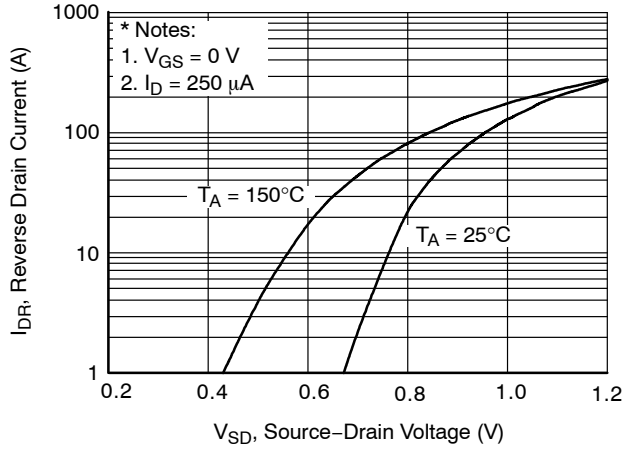


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

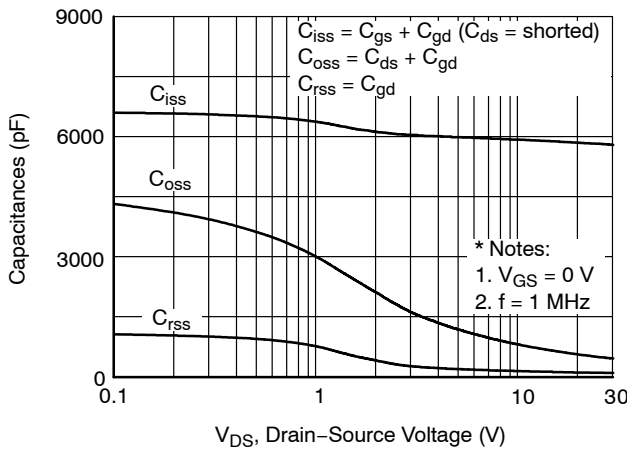


Figure 5. Capacitance Characteristics

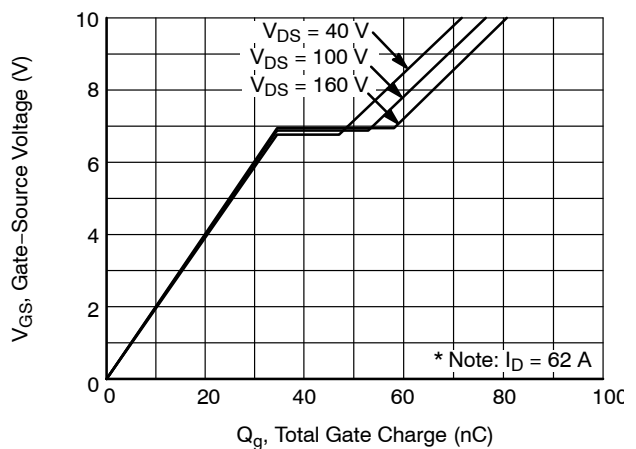


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

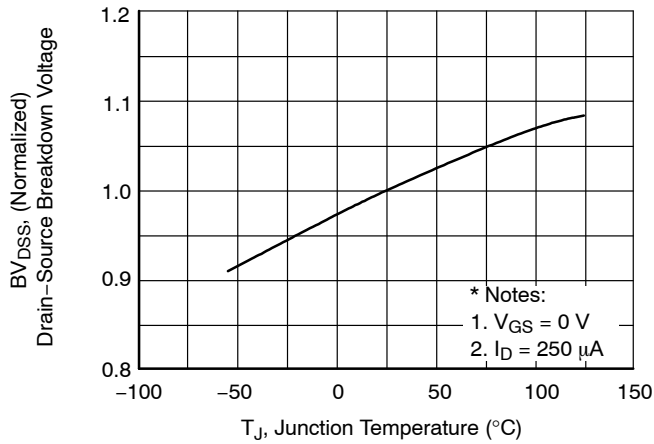


Figure 7. Breakdown Voltage Variation vs. Temperature

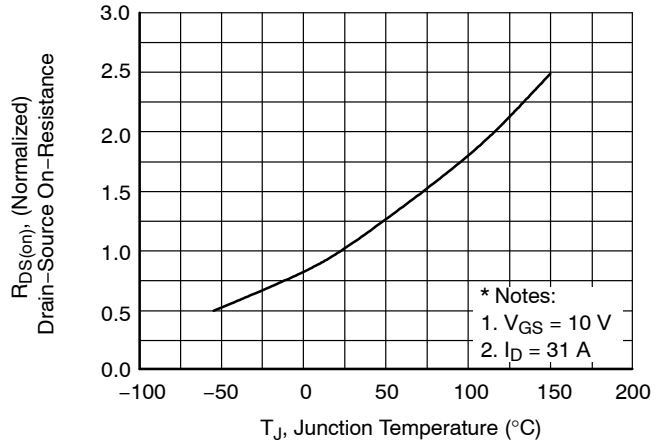


Figure 8. On-Resistance Variation vs. Temperature

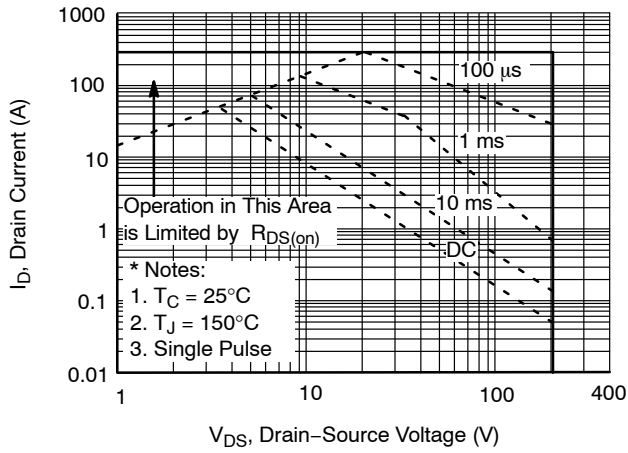


Figure 9. Maximum Safe Operating Area

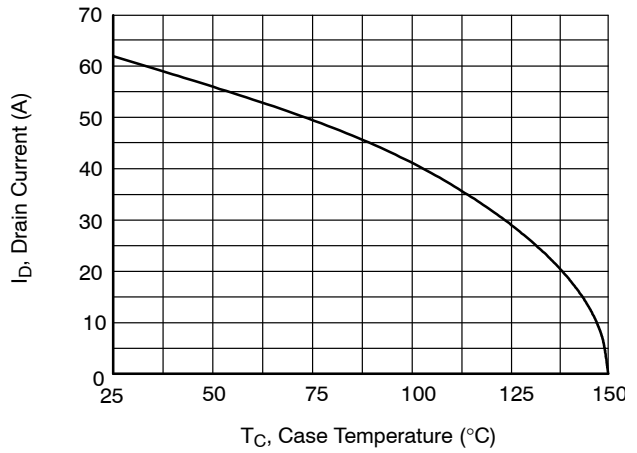


Figure 10. Maximum Drain Current vs. Case Temperature

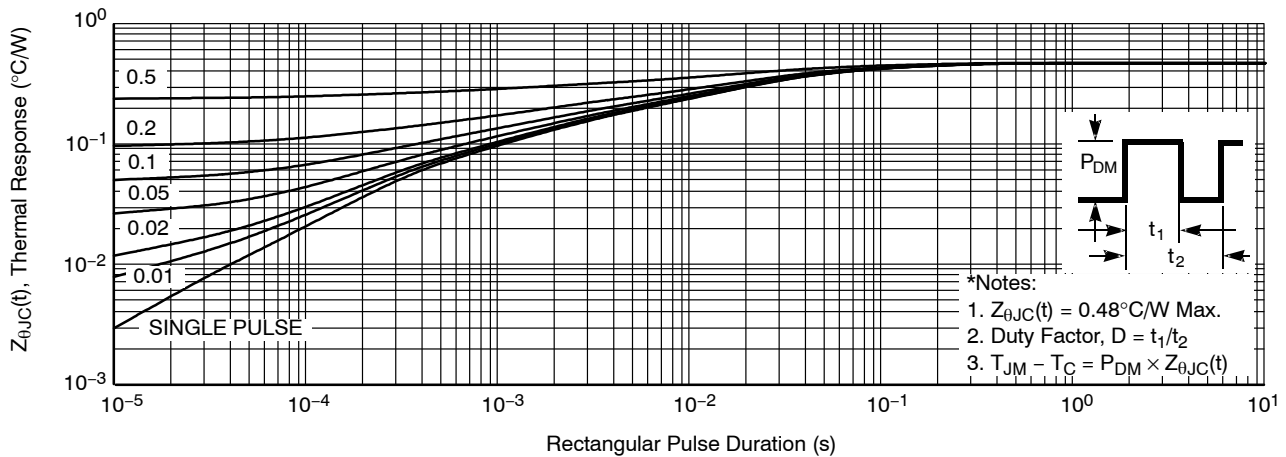


Figure 11. Transient Thermal Response Curve

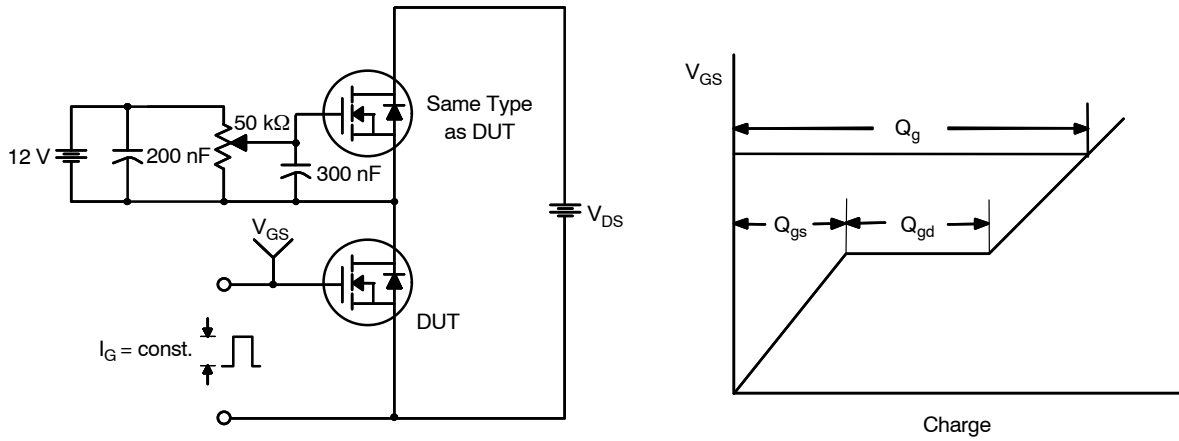


Figure 12. Gate Charge Test Circuit & Waveform

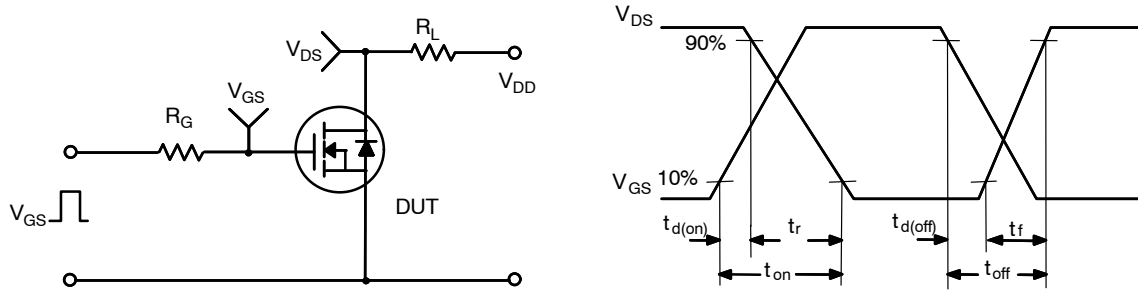


Figure 13. Resistive Switching Test Circuit & Waveforms

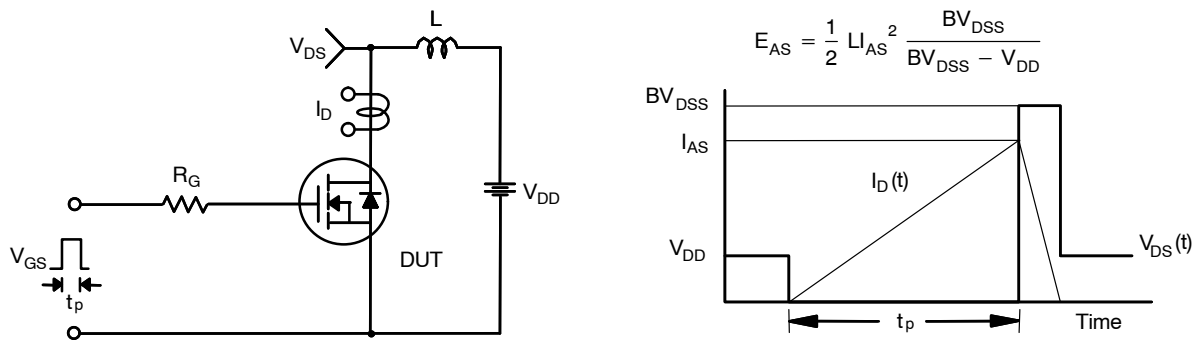
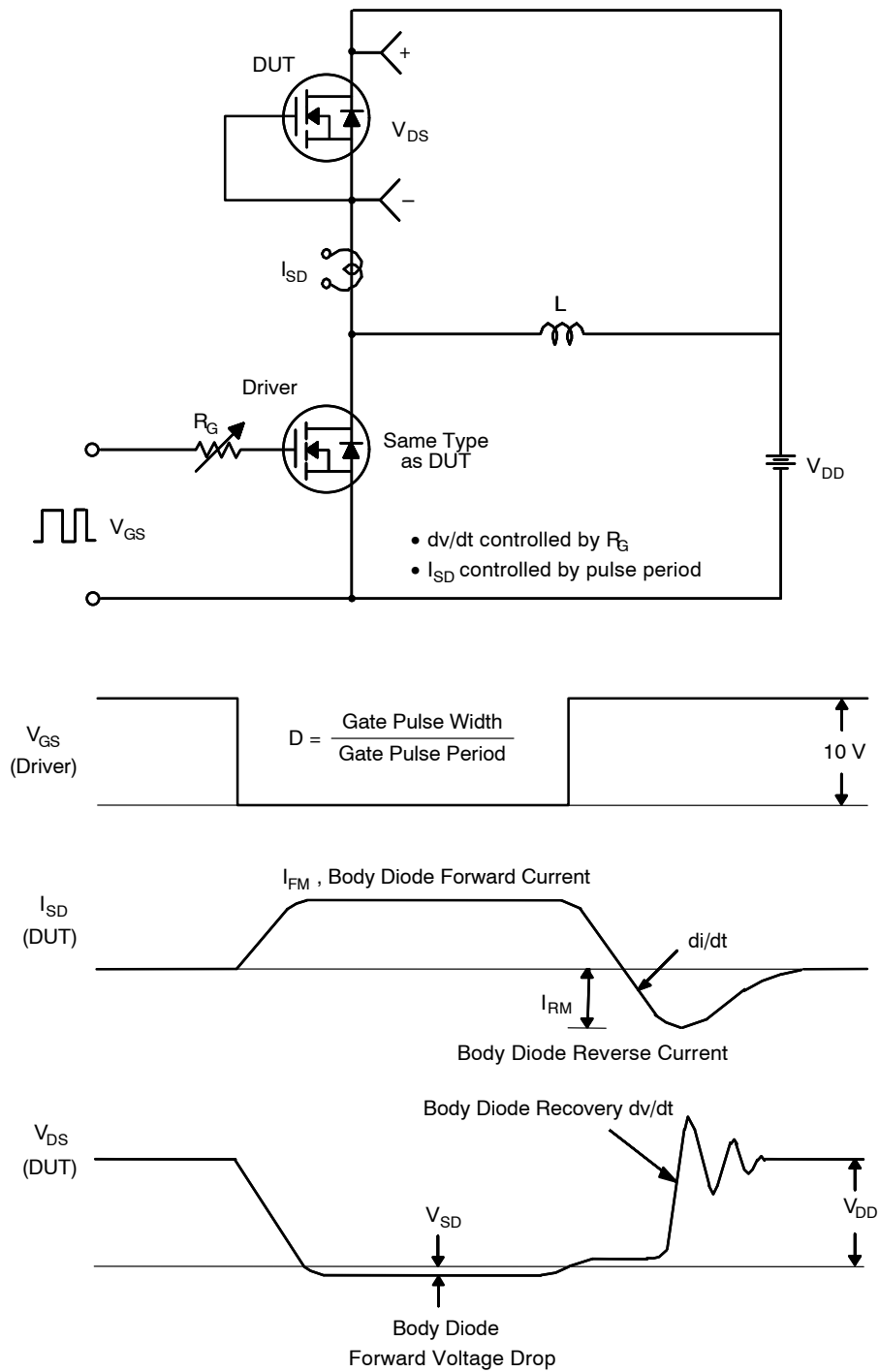
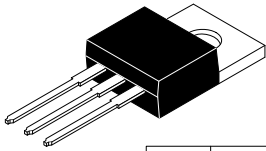


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

# FDP2614



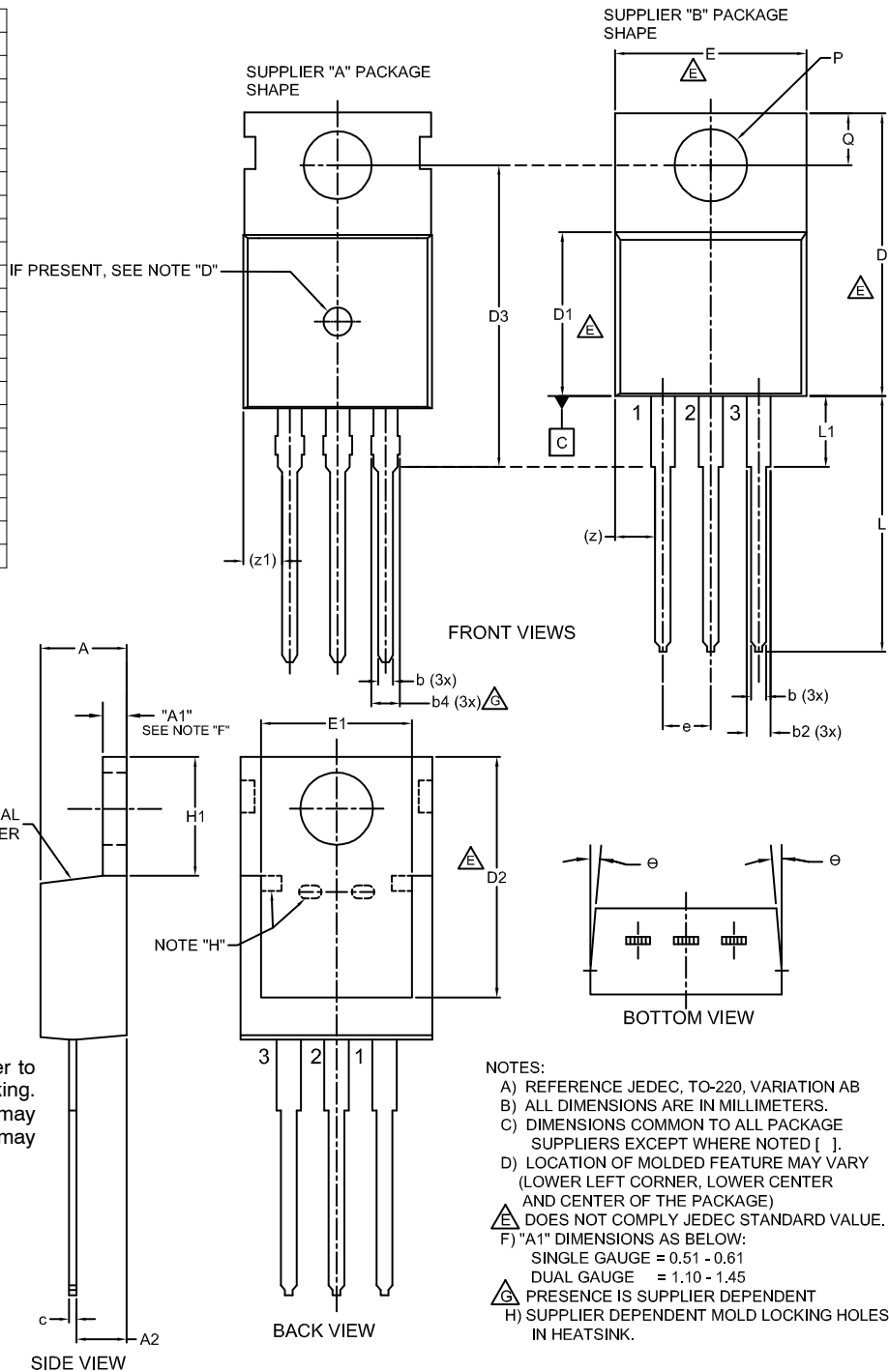
**Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms**



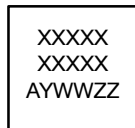
TO-220-3LD  
CASE 340AT  
ISSUE B

DATE 08 AUG 2022

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.00	--	4.70
A1	SEE NOTE "F"		
A2	2.10	--	2.85
b	0.55	--	1.00
b2	1.10	--	1.62
b4	1.42	--	1.62
c	0.36	--	0.60
D	13.90	--	16.30
D1	8.13	--	9.40
D2	11.50	--	14.30
D3	15.42	--	16.51
E	9.65	--	10.67
E1	7.59	--	8.65
e	2.40	--	2.67
H1	6.06	--	6.69
L	12.70	--	14.04
L1	2.70	--	4.10
P	3.50	--	4.00
Q	2.50	--	3.40
z	2.13 REF		
z1	2.06 REF		
θ	3°	--	5°



GENERIC MARKING DIAGRAM\*



XXXX = Specific Device Code  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 ZZ = Assembly Lot Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

- A) REFERENCE JEDEC, TO-220, VARIATION AB
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
- D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
- ⚠ DOES NOT COMPLY JEDEC STANDARD VALUE.
- F) "A1" DIMENSIONS AS BELOW:  
 SINGLE GAUGE = 0.51 - 0.61  
 DUAL GAUGE = 1.10 - 1.45
- ⚠ PRESENCE IS SUPPLIER DEPENDENT
- H) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

DOCUMENT NUMBER:	98AON13818G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-220-3LD	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at [www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)

